Silicon NPN Power Transistors BU508AW

DESCRIPTION

·With TO-247 package

·High voltage

·High speed switching

APPLICATIONS

·For use in horizontal deflection circuits
of colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

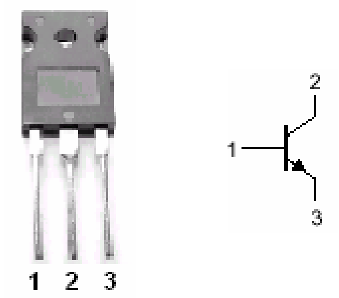

Fig.1 simplified outline (TO-247) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
I_C	Collector current (DC)		8	A
I_{CM}	Collector current -peak		15	A
I_B	Base current (DC)		4	A
I_{BM}	Base current -peak		6	A
P_{tot}	Total power dissipation	T_C=25□	125	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0,L=25mH	700			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4.5A ;I_B=1.6A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4.5A ;I_B=2A			1.1	V
I_{CES}	Collector cut-off current	V_{CE}=Rated$V_{CE;}$ V_{BE}=0 T_C=125℃			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6.0V; I_C=0			10	mA
h_{FE}	DC current gain	I_C=100mA ; V_{CE}=5V	6	13	30	
f_T	Transition frequency	I_E=0.1A ; V_{CE}=5V		7		MHz
Cob	Output capacitance	V_{CB}=10V;I_E=0;f=1.0MHz		125		pF

PACKAGE OUTLINE

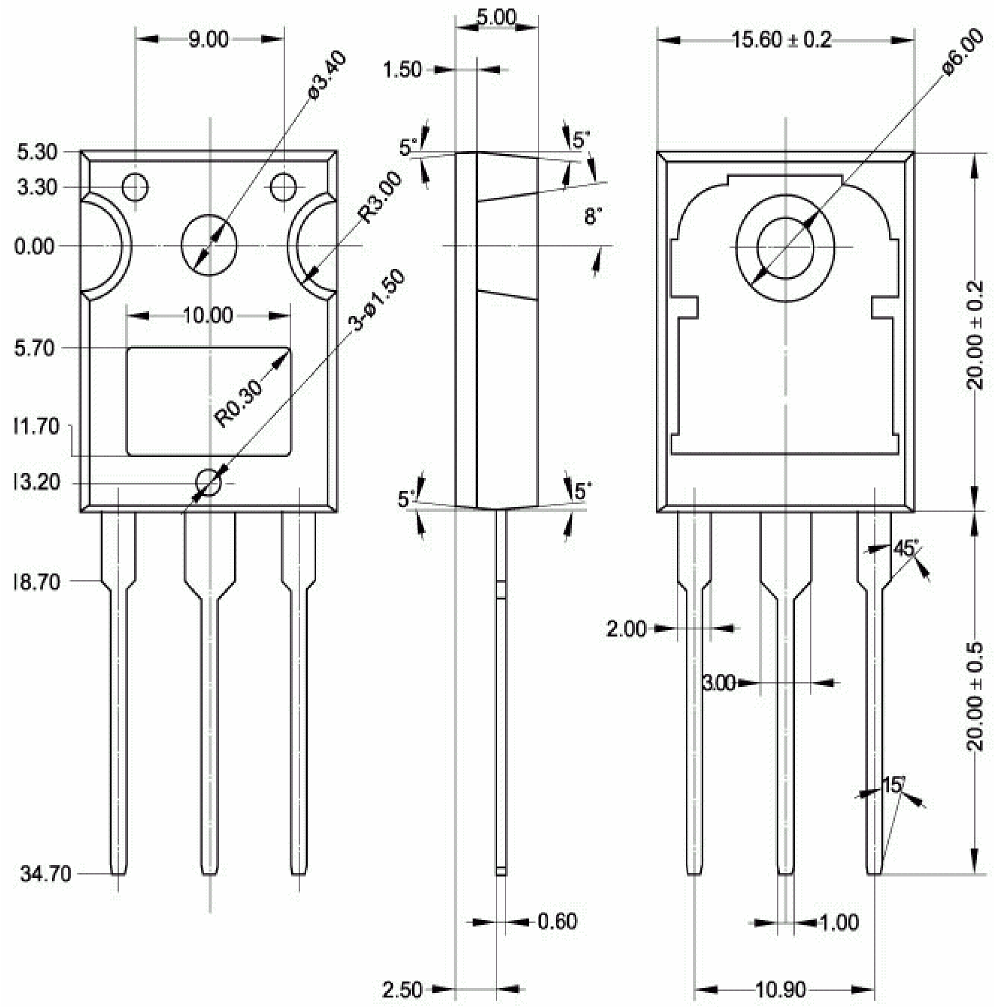

Fig.2 Outline dimensions